Yoichi Yamada

List of Publications by Year
in descending order

135	2,165	25	41
papers	citations	h-index	g-index
		236925	276875

135	135	135	1484
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Internal quantum efficiency of highly-efficient InxGa1â^'xN-based near-ultraviolet light-emitting diodes. Applied Physics Letters, 2003, 83, 4906-4908.	3.3	275
2	Cerium oxide and hydrogen co-doped indium oxide films for high-efficiency silicon heterojunction solar cells. Solar Energy Materials and Solar Cells, 2016, 149, 75-80.	6.2	92
3	13 mW operation of a 295â€"310 nm AlGaN UV-B LED with a p-AlGaN transparent contact layer for real world applications. Journal of Materials Chemistry C, 2019, 7, 143-152.	5.5	84
4	Ultraviolet stimulated emission and optical gain spectra in CdxZn1â^'xSâ€ZnS strainedâ€layer superlattices. Applied Physics Letters, 1992, 61, 2190-2192.	3.3	76
5	Internal Quantum Efficiency and Nonradiative Recombination Rate in InGaN-Based Near-Ultraviolet Light-Emitting Diodes. Japanese Journal of Applied Physics, 2012, 51, 072102.	1.5	62
6	Recombination dynamics of localized excitons in a CdSe/ZnSe/ZnSxSe1â^'xsingle-quantum-well structure. Physical Review B, 1996, 54, 2629-2634.	3.2	46
7	Dependence of internal quantum efficiency on doping region and Si concentration in Al-rich AlGaN quantum wells. Applied Physics Letters, 2012, 101, 042110.	3.3	45
8	External Quantum Efficiency of 6.5% at 300 nm Emission and 4.7% at 310 nm Emission on Bare Wafer of AlGaN-Based UVB LEDs. ACS Applied Electronic Materials, 2020, 2, 1892-1907.	4.3	45
9	Band Offsets in CdZnS/ZnS Strained-Layer Quantum Well and Its Application to UV Laser Diode. Japanese Journal of Applied Physics, 1993, 32, L1308-L1311.	1.5	44
10	Localized excitons in cubicZn1â^'xCdxS lattice matched to GaAs. Physical Review B, 1994, 50, 14655-14658.	3.2	43
11	Internal Quantum Efficiency and Nonradiative Recombination Rate in InGaN-Based Near-Ultraviolet Light-Emitting Diodes. Japanese Journal of Applied Physics, 2012, 51, 072102.	1.5	43
12	Controlling potential barrier height by changing V-shaped pit size and the effect on optical and electrical properties for InGaN/GaN based light-emitting diodes. Journal of Applied Physics, 2015, 117, .	2.5	40
13	Biexciton luminescence from cubic ZnS epitaxial layers. Applied Physics Letters, 1996, 69, 88-90.	3.3	39
14	Biexciton Luminescence from GaN Epitaxial Layers. Japanese Journal of Applied Physics, 1996, 35, L787-L789.	1.5	38
15	Effects of exciton localization on internal quantum efficiency of InGaN nanowires. Journal of Applied Physics, 2013, 114, .	2.5	38
16	Achieving 9.6% efficiency in 304Ânm p-AlGaN UVB LED via increasing the holes injection and light reflectance. Scientific Reports, 2022, 12, 2591.	3.3	38
17	Interface properties and the effect of strain of ZnSe/ZnS strained-layer superlattices. Physica B: Condensed Matter, 1993, 191, 23-44.	2.7	36
18	Type conversion under hydrostatic pressure in ZnSe-ZnS strained-layer superlattices. Physical Review B, 1991, 44, 1801-1805.	3.2	35

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19	Optical properties of biexcitons in ZnS. Physical Review B, 2000, 61, 8363-8368.	3.2	34
20	Temperature dependence of localized exciton transitions in AlGaN ternary alloy epitaxial layers. Journal of Applied Physics, 2008, 104, .	2.5	33
21	Time-resolved nonlinear luminescence of biexcitons in ZnSe-ZnxMg1â^'xSySe1â^'ysingle quantum wells. Physical Review B, 1995, 52, R2289-R2292.	3.2	32
22	Photoluminescence from highly excited AlN epitaxial layers. Applied Physics Letters, 2008, 92, .	3.3	31
23	Temperature dependence of Stokes shift in InxGa1â^'xN epitaxial layers. Journal of Applied Physics, 2003, 93, 1642-1646.	2.5	30
24	Temperature dependence of free-exciton luminescence in cubic CdS films. Applied Physics Letters, 2003, 82, 388-390.	3.3	30
25	High internal quantum efficiency and optically pumped stimulated emission in AlGaN-based UV-C multiple quantum wells. Applied Physics Letters, 2020, 117, .	3.3	28
26	Time-resolved spectroscopy of biexciton luminescence inZnxCd1â^'xSe-ZnSySe1â^'ymultiple quantum wells. Physical Review B, 1995, 51, 2596-2599.	3.2	26
27	Beyond 53% internal quantum efficiency in a AlGaN quantum well at 326â€‰â€‰nm UVA emission and single-peak operation of UVA LED. Optics Letters, 2020, 45, 495.	3.3	26
28	Temperature dependence of excitonic luminescence from high-quality ZnS epitaxial layers. Journal of Crystal Growth, 1998, 184-185, 1110-1113.	1.5	25
29	Bound-Exciton and Edge-Emission Spectra Associated with Li and Na Acceptors in ZnSe. Japanese Journal of Applied Physics, 1989, 28, L837-L840.	1.5	24
30	AlN homoepitaxial growth on sublimation-AlN substrate by low-pressure HVPE. Journal of Crystal Growth, 2012, 350, 69-71.	1.5	24
31	Stokes shift of biexcitons inAlxGa1â^'xNepitaxial layers. Physical Review B, 2004, 70, .	3.2	23
32	Correlation between excitons recombination dynamics and internal quantum efficiency of AlGaN-based UV-A multiple quantum wells. Journal of Applied Physics, 2020, 128, .	2.5	23
33	Formation of optical gain due to exciton localization in CdxZn1â^'xS-ZnS strained-layer quantum wells. Physica B: Condensed Matter, 1993, 191, 83-89.	2.7	22
34	Intense Ultraviolet Electroluminescence Properties of the High-Power InGaN-Based Light-Emitting Diodes Fabricated on Patterned Sapphire Substrates. Japanese Journal of Applied Physics, 2002, 41, 2484-2488.	1.5	22
35	Excitonic luminescence and the effect of high excitation in ZnSeî—¸ZnS strained-layer superlattices grown on ZnS substrates. Journal of Crystal Growth, 1990, 101, 661-666.	1.5	21
36	Inhomogeneous distribution of defect-related emission in Si-doped AlGaN epitaxial layers with different Al content and Si concentration. Journal of Applied Physics, 2014, 115, .	2.5	21

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37	Biaxial splitting of optical phonon modes in ZnSeâ€ZnS strainedâ€layer superlattices. Applied Physics Letters, 1991, 58, 2135-2137.	3.3	20
38	Free excitons in cubic CdS films. Applied Physics Letters, 2002, 80, 267-269.	3.3	20
39	Biexciton luminescence from AlxGa1âˆ'xN epitaxial layers. Applied Physics Letters, 2004, 84, 2082-2084.	3.3	18
40	Ultraviolet stimulated emission due to biexciton decay process in ZnS-based quantum wells. Applied Physics Letters, 1997, 70, 1429-1431.	3.3	17
41	Room-temperature 340nm ultraviolet electroluminescence from ZnS-based light-emitting diodes. Journal of Crystal Growth, 2000, 214-215, 1091-1095.	1.5	17
42	Temperature dependence of excitonic transitions in a-plane AlN epitaxial layers. Journal of Applied Physics, 2009, 105, 083533.	2.5	17
43	Growth of Bulk GaN Single Crystals by the Pressure-Controlled Solution Growth Method. Japanese Journal of Applied Physics, 2000, 39, 2394-2398.	1.5	16
44	Spatially separated intrinsic emission components in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>In</mml:mtext></mml:mrow><mml:mi>x</mml:mi></mml:msub> alloys. Physical Review B, 2009, 80, .	3.2	16
45	Excitation density dependence of radiative and nonradiative recombination lifetimes in InGaN/GaN multiple quantum wells. Physica Status Solidi (B): Basic Research, 2015, 252, 940-945.	1.5	16
46	Excitonic Properties of ZnSe-ZnS Strained-Layer Superlattices and A Fibonacci Sequence. Materials Research Society Symposia Proceedings, 1989, 161, 199.	0.1	14
47	Time-resolved spectroscopy of biexciton luminescence in wide-bandgap II-VI quantum wells. Superlattices and Microstructures, 1994, 15, 33.	3.1	14
48	Localization-induced inhomogeneous screening of internal electric fields in AlGaN-based quantum wells. Applied Physics Letters, 2007, 91, .	3.3	14
49	Silicon concentration dependence of optical polarization in AlGaN epitaxial layers. Applied Physics Letters, 2011, 98, .	3.3	14
50	Internal Quantum Efficiency of Nitride-based Light-Emitting Diodes. Journal of Light and Visual Environment, 2008, 32, 191-195.	0.2	14
51	Time-resolved spectroscopy of excitonic luminescence from GaN homoepitaxial layers. Journal of Applied Physics, 1999, 86, 7186-7188.	2.5	13
52	Separation of effects of InGaN/GaN superlattice on performance of light-emitting diodes using mid-temperature-grown GaN layer. Japanese Journal of Applied Physics, 2018, 57, 062101.	1.5	13
53	Potential Barrier Formed Around Dislocations in InGaN Quantum Well Structures by Spot Cathodoluminescence Measurements. Physica Status Solidi (B): Basic Research, 2018, 255, 1700358.	1.5	13
54	Recombination dynamics of carriers in an InGaN/AlGaN single-quantum-well light-emitting diode under reverse-bias voltages. Applied Physics Letters, 2000, 76, 1546-1548.	3.3	12

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55	Optically pumped CdZnSe/ZnSe blueâ€green vertical cavity surface emitting lasers. Applied Physics Letters, 1995, 66, 2929-2931.	3.3	11
56	Excitonic Emissions under High Excitation of Hexagonal GaN Single Crystal Grown by Sublimation Method. Japanese Journal of Applied Physics, 1999, 38, L102-L104.	1.5	11
57	Analysis of efficiency curves in near-UV, blue, and green-emitting InGaN-based multiple quantum wells using rate equations of exciton recombination. Japanese Journal of Applied Physics, 2019, 58, SCCB02.	1.5	11
58	Dense excitonic luminescence and optical gain in ZnS-based quantum wells. Journal of Luminescence, 2000, 87-89, 140-144.	3.1	9
59	Emission Wavelength Dependence of Internal Quantum Efficiency in InGaN Nanowires. Japanese Journal of Applied Physics, 2013, 52, 08JE10.	1.5	9
60	Effects of Si-doping on luminescence properties of InxGa1âˆ'xN epitaxial layers. Journal of Crystal Growth, 1998, 189-190, 611-615.	1.5	8
61	Photoluminescence characterization of MBE-grown ZnTexSe1âˆ'x epitaxial layers with high Te concentrations. Journal of Crystal Growth, 2000, 214-215, 220-224.	1.5	8
62	Huge binding energy of localized biexcitons in Al-rich AlxGa1âˆ'xN ternary alloys. Applied Physics Letters, 2011, 98, 081907.	3.3	8
63	Photoluminescence due to Inelastic Biexciton Scattering from an Al$_{0.61}$Ga$_{0.39}$N Ternary Alloy Epitaxial Layer at Room Temperature. Applied Physics Express, 2012, 5, 072401.	2.4	8
64	Correlation between in-plane strain and optical polarization of Si-doped AlGaN epitaxial layers as a function of Al content and Si concentration. Journal of Applied Physics, 2012, 112, 033512.	2.5	8
65	Binding energy of localized biexcitons in AlGaN-based quantum wells. Applied Physics Express, 2014, 7, 122101.	2.4	8
66	High-temperature photoluminescence and photoluminescence excitation spectroscopy of Al_{0.60}Ga_{0.40}N/Al_{0.70}Ga_{0.30}N multiple quantum wells. Applied Physics Express, 2017, 10, 021002.	2.4	8
67	Epitaxial growth and photoluminescence characterization of ZnSe: Na films by low-pressure MOCVD. Journal of Crystal Growth, 1990, 99, 408-412.	1.5	7
68	Structural Characterization of High-Quality ZnS Epitaxial Layers Grown on GaAs Substrates by Low-Pressure Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2001, 40, 6993-6997.	1.5	7
69	Nanoscopic spectroscopy of potential barriers formed around V-pits in InGaN/GaN multiple quantum wells on moderate temperature GaN pit expansion layers. Journal of Applied Physics, 2018, 124, .	2.5	7
70	Effects of saturation of nonradiative recombination centers on internal quantum efficiency in InGaN light-emitting diodes. Japanese Journal of Applied Physics, 2019, 58, 011003.	1.5	7
71	Beyond 53% internal quantum efficiency in a AlGaN quantum well at 326â€‰â€‰nm UVA emission and single-peak operation of UVA LED: publisherâ€™s note. Optics Letters, 2020, 45, 2563.	3.3	7
72	Ultraviolet lasing and excitonic gain in CdxZn1âˆ'xS-ZnS strained-layer multiple quantum wells. Journal of Crystal Growth, 1994, 138, 570-574.	1.5	6

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73	Excitonic Emission in GaN Films on AlN Substrates Using Microwave-Excited N Plasma Method. Japanese Journal of Applied Physics, 1996, 35, 1424-1427.	1.5	6
74	Recombination dynamics of localized excitons in AlxGa1-xN (0.37<x<0.81) ternary alloys. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2133-2135.	0.8	6
75	Structural and optical evaluation of InGaN/GaN multi-quantum wells on template consisting of in-plane alternately arranged relaxed InGaN and GaN. Journal of Applied Physics, 2012, 111, 043508.	2.5	6
76	Cathodoluminescence Study of Optical Inhomogeneity in Si-Doped AlGaN Epitaxial Layers Grown by Low-Pressure Metalorganic Vapor-Phase Epitaxy. Japanese Journal of Applied Physics, 2013, 52, 08JL07.	1.5	6
77	Evaluation of internal quantum efficiency and stimulated emission characteristics in AlGaN-based multiple quantum wells. Japanese Journal of Applied Physics, 2021, 60, 120503.	1.5	6
78	Extremely high internal quantum efficiency of AlGaN-based quantum wells on face-to-face annealed sputter-deposited AlN templates. Applied Physics Express, 2021, 14, 122004.	2.4	6
79	Luminescence properties of lithium-doped ZnS epitaxial layers grown by MOCVD. Journal of Crystal Growth, 2002, 237-239, 1570-1574.	1.5	5
80	Spatially resolved cathodoluminescence study on AlGaN layer fabricated by air-bridged lateral epitaxial growth. Physica Status Solidi (B): Basic Research, 2004, 241, 2730-2734.	1.5	5
81	Dynamics of biexciton localization in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>Al</mml:mtext></mml:mrow><mml:mi>x</mml:mi></mml:msub> crystals under exciton resonant excitation. Physical Review B, 2008, 77, .	3.2	5
82	Ultrafast decay of photoluminescence from high-density excitons inAlxGa1â^'xNmixed crystals: Diffusive propagation of exciton-polaritons. Physical Review B, 2010, 82, .	3.2	5
83	Si concentration dependence of structural inhomogeneities in Si-doped Al<i>x</i>Ga1â^'<i>x</i>N/Al<i>y</i>Ga1â^'<i>y</i>N multiple quantum well structures (<i>x</i>â€‰=â€‰0.6) and its relationship with internal quantum efficiency. Journal of Applied Physics, 2014, 116, .	2.5	5
84	Microscopic potential fluctuations in Si-doped AlGaN epitaxial layers with various AlN molar fractions and Si concentrations. Journal of Applied Physics, 2016, 119, .	2.5	5
85	Hydrostatic-pressure-induced type-I â†' type-II conversion in ZnSe-ZnS strained-layer superlattices. Journal of Crystal Growth, 1992, 117, 484-487.	1.5	4
86	New characterization method of biaxial stress by Raman scattering: demonstration in ZnSe-ZnS strained-layer superlattices. Journal of Crystal Growth, 1992, 117, 488-491.	1.5	4
87	Optical and structural properties of high-quality ZnS epitaxial layers grown on GaAs substrates by low-pressure metalorganic chemical vapor deposition. Journal of Crystal Growth, 2000, 221, 388-392.	1.5	4
88	Temperature Dependence of Stokes Shifts of Excitons and Biexcitons in Al_{0.61}Ga_{0.39}N Epitaxial Layer. Physica Status Solidi (B): Basic Research, 2018, 255, 1700374.	1.5	4
89	Temperature dependence of excitonic transitions in Al0.60Ga0.40N/Al0.70Ga0.30N multiple quantum wells from 4 to 750â€‰K. Journal of Applied Physics, 2018, 123, .	2.5	4
90	Hydrostatic pressure dependence of two-dimensional exciton luminescence in ZnSe/ZnS strained-layer superlattices. Surface Science, 1992, 267, 129-132.	1.9	3

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91	Blue radiative recombination due to hot electrons in InGaN single-quantum well LEDs. Journal of Crystal Growth, 1998, 189-190, 812-815.	1.5	3
92	Dependence of Exciton -- Longitudinal-Optical-Phonon Interaction Energy on Well Width in Cd0.2Zn0.8Se/ZnSe Multiple-Quantum Wells. Japanese Journal of Applied Physics, 1999, 38, L808-L810.	1.5	3
93	Reduction of Inhomogeneous Broadening of Exciton Luminescence in CdxZn1-xSe Ternary Alloys and CdxZn1-xSeâ€"ZnSe Multiple Quantum Wells Grown by Molecular-Beam Epitaxy under Se-Excess Supply. Japanese Journal of Applied Physics, 1999, 38, 3550-3555.	1.5	3
94	Effects of electric field on photoluminescence spectra in InGaN ultraviolet light-emitting diodes. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 949-952.	2.7	3
95	Temperature dependence of electric-field induced photoluminescence from an InGaN-based light-emitting diode. Journal of Applied Physics, 2001, 89, 5779-5781.	2.5	3
96	Time-resolved nonlinear luminescence of excitonic transitions in GaN. Journal of Applied Physics, 2004, 96, 138-143.	2.5	3
97	Population dynamics of localized biexcitons in AlxGa1â^'xN ternary alloys. Applied Physics Letters, 2007, 91, .	3.3	3
98	Composition dependent dynamics of biexciton localization in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>Al</mml:mtext></mml:mrow><mml:mi>x</mml:mi></mml:msub> crystals. Physical Review B, 2009, 80, .	3.2	3
99	Exciton localization in Alâ€rich AlGaN ternary alloy epitaxial layers. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 1884-1886.	0.8	3
100	Spatially Resolved Spectroscopy of Blue and Green InGaN Quantum Wells by Scanning Nearâ€Field Optical Microscopy. Physica Status Solidi (B): Basic Research, 2018, 255, 1700322.	1.5	3
101	Recent Progress Toward Realizing AlGaN-Based Deep-UV Laser Diodes. The Review of Laser Engineering, 2019, 47, 196.	0.0	3
102	Effect of Strain on Bound Excitons in High-Purity ZnSe Bulk and MOCVD Homoepitaxially-Grown ZnSe Layer. Materials Research Society Symposia Proceedings, 1987, 102, 143.	0.1	2
103	Structural properties and intense ultraviolet emission of polycrystalline GaN films on AlN ceramics grown by N plasma-excited CVD. Journal of Crystal Growth, 1998, 189-190, 223-226.	1.5	2
104	Recombination dynamics of localized biexcitons in AlGaN ternary alloys (Invited Paper). , 2005, , .		2
105	Recombination dynamics and internal quantum efficiency in InGaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 652-655.	0.8	2
106	Confinement-enhanced biexciton binding energy in AlGaN-based quantum wells. Applied Physics Express, 2017, 10, 051003.	2.4	2
107	Cathodoluminescence study on local high-energy emissions at dark spots in AlGaN/AlGaN multiple quantum wells. Japanese Journal of Applied Physics, 2018, 57, 060311.	1.5	2
108	Recombination Dynamics of Self-Trapped Excitons in the High-Efficient Blue LEDs under Reverse Bias Condition. , 1999, , .		2

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109	Highly Transparent pâ€AlGaNâ€Based (326â€"341 nm)â€Band Ultravioletâ€A Lightâ€Emitting Diodes on AlN Templates: Recent Advances and Perspectives. Physica Status Solidi (A) Applications and Materials Science, 2022, 219, .	1.8	2
110	Effect of external uniaxial stress on the green-blue emission of a CdZnSe strained quantum well under high excitation. Journal of Crystal Growth, 1996, 159, 676-679.	1.5	1
111	Effect of High Current Injection on the Blue Radiative Recombination in InGaN Single Quantum Well Light Emitting Diodes. Japanese Journal of Applied Physics, 1998, 37, 1462-1464.	1.5	1
112	Magneto-luminescence spectroscopy of biexcitons in ZnS epitaxial layers. Journal of Crystal Growth, 2000, 214-215, 815-818.	1.5	1
113	Ultraviolet emission properties in InxGa1â^'xN epitaxial layer revealed by magnetoluminescence and time-resolved luminescence studies. Journal of Luminescence, 2000, 87-89, 1199-1201.	3.1	1
114	Recombination dynamics of localized excitons in AlGaN-based quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2274-2276.	0.8	1
115	Spatial Inhomogeneity of Aluminum Content in Air-Bridged Lateral Epitaxially Grown AlGaN Ternary Alloy Films Probed by Cross-Sectional Scanning Near-Field Optical Microscopy. Japanese Journal of Applied Physics, 2012, 51, 035604.	1.5	1
116	Optical Properties of ZnCdS:I Orange and ZnSTe:I White Thin Film Phosphor for High Ra White LED. Journal of Light and Visual Environment, 2007, 31, 61-64.	0.2	1
117	Effects of high excitation on localized excitons in cubic ZnCdS lattice matched to GaAs. Journal of Crystal Growth, 1996, 159, 830-834.	1.5	0
118	Dynamics of dense excitonic systems in ZnSe-based single quantum wells. Journal of Crystal Growth, 1996, 159, 814-817.	1.5	0
119	Localized biexcitons and optical gain in ZnS-based quantum wells. Electronics and Communications in Japan, 1999, 82, 64-72.	0.2	0
120	Defect identification in homoepitaxial- and ELO-grown GaN layers using bound-exciton Zeeman spectroscopies. Journal of Crystal Growth, 2000, 210, 216-219.	1.5	0
121	Radiative recombination mechanisms in InGaN/AlGaN single-quantum-well LED revealed by time-resolved photoluminescence spectra under external electric fields. , 2000, , .		0
122	Fundamental Properties of Wide Bandgap Semiconductors. , 2007, , 25-96.		0
123	Discrete luminescence bands in AlGaN-based quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S767-S771.	0.8	0
124	Localization dynamics of biexcitons and electronâ€"hole plasmas in GaNâ€based mixed crystals. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 33-36.	1.8	0
125	Recombination dynamics of excitons in phosphorus-doped ZnO nanostructures. , 2010, , .		0
126	Bowing of biexciton binding in Al x Ga 1-x N ternary alloys. Proceedings of SPIE, 2011, , .	0.8	0

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127	Ultraviolet biexcitonic emission from AlGaN ternary alloys. Electronics and Communications in Japan, 2011, 94, 41-47.	0.5	0
128	Fabrication and Evaluation of GaN Layer Composed ofm- and {1011} Facet Structure. Japanese Journal of Applied Physics, 2013, 52, 01AF06.	1.5	0
129	Temperature-dependent cathodoluminescence mapping of InGaN epitaxial layers with different In compositions. Japanese Journal of Applied Physics, 2019, 58, SCCB13.	1.5	0
130	Study on higher-energy emission observed locally around V-pits on InGaN/GaN quantum wells grown on moderate-temperature GaN. Journal of Applied Physics, 2021, 130, 053103.	2.5	0
131	Ultraviolet Biexcitonic Emission from AlGaN Ternary Alloys. IEEJ Transactions on Electronics, Information and Systems, 2008, 128, 757-762.	0.2	0
132	Spatial Inhomogeneity of Aluminum Content in Air-Bridged Lateral Epitaxially Grown AlGaN Ternary Alloy Films Probed by Cross-Sectional Scanning Near-Field Optical Microscopy. Japanese Journal of Applied Physics, 2012, 51, 035604.	1.5	0
133	Time and Spatially Resolved Luminescence Spectroscopy of ZnO Nanostructures. Springer Series in Materials Science, 2014, , 195-216.	0.6	0
134	Blue Semiconductor Lasers. Lasing Mechanism of Blue and Ultraviolet Semiconductor Lasers.. The Review of Laser Engineering, 1997, 25, 493-497.	0.0	0
135	Improvement of high laser-resistance surface in CLBO by ion beam etching. The Review of Laser Engineering, 1999, 27, 123-125,128.	0.0	0